



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



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## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>c</sub> = +25°C (Note 11)
80V	3.8mΩ @ V <sub>GS</sub> = 10V	100A
	5.3mΩ @ V <sub>GS</sub> = 4.5V	100A

## Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> – Minimizes On-State Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**

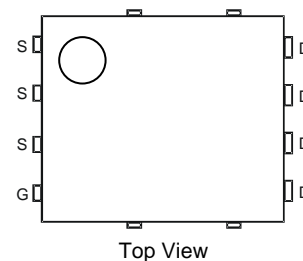
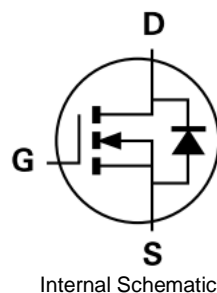
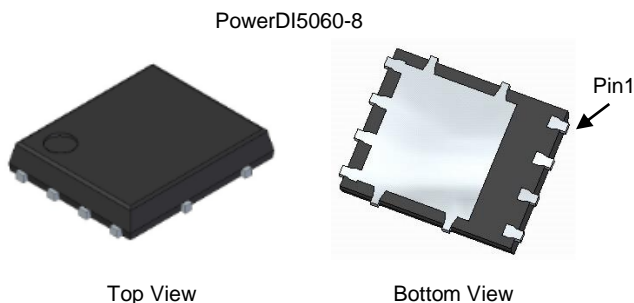
## Description and Applications

This new generation MOSFET is designed to minimize R<sub>DS(ON)</sub>, yet maintain superior switching performance. This device is ideal for use in power management and load switch.

- DC-DC Converters
- Load Switch

## Mechanical Data

- Case: PowerDI<sup>®</sup>5060-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 <sup>Ⓔ</sup>
- Weight: 0.097 grams (Approximate)



**Maximum Ratings** (@T<sub>c</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		V <sub>DSS</sub>	80	V	
Gate-Source Voltage		V <sub>GSS</sub>	±20	V	
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 7)	Steady State	I <sub>D</sub>	T <sub>C</sub> = +25°C	100	A
			T <sub>C</sub> = +100°C (Note 11)	100	
Maximum Continuous Body Diode Forward Current (Note 7)		I <sub>S</sub>	83	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	400	A	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	400	A	
Avalanche Current, L = 0.3mH (Note 8)		I <sub>AS</sub>	35	A	
Avalanche Energy, L = 0.3mH (Note 8)		E <sub>AS</sub>	183.7	mJ	

**Thermal Characteristics** (@T<sub>c</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	101	°C/W
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.9	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	51	°C/W
Total Power Dissipation (Note 7)	T <sub>C</sub> = +25°C	P <sub>D</sub>	125	W
Thermal Resistance, Junction to Case (Note 7)		R <sub>θJC</sub>	1.2	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

**Electrical Characteristics** (@T<sub>c</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 9)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	80	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 64V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 9)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.3	—	2.8	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	2.8	3.8	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		—	3.9	5.3		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>iSS</sub>	—	4979	—	pF	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oSS</sub>	—	1166	—		
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	71	—		
Gate Resistance	R <sub>G</sub>	—	2.1	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>	—	43	—	nC	V <sub>DD</sub> = 40V, I <sub>D</sub> = 20A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>G</sub>	—	81	—		
Gate-Source Charge	Q <sub>GS</sub>	—	14	—		
Gate-Drain Charge	Q <sub>GD</sub>	—	22	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	8.5	—	ns	V <sub>DD</sub> = 40V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A, R <sub>G</sub> = 1.6Ω
Turn-On Rise Time	t <sub>R</sub>	—	11.8	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	55	—		
Turn-Off Fall Time	t <sub>F</sub>	—	27.7	—		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	—	53	—	ns	I <sub>F</sub> = 20A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	—	91	—	nC	

- Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  7. Thermal resistance from junction to soldering point (on the exposed drain pad).
  8. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  9. Short duration pulse test used to minimize self-heating effect.
  10. Guaranteed by design. Not subject to product testing.
  11. Package limited.

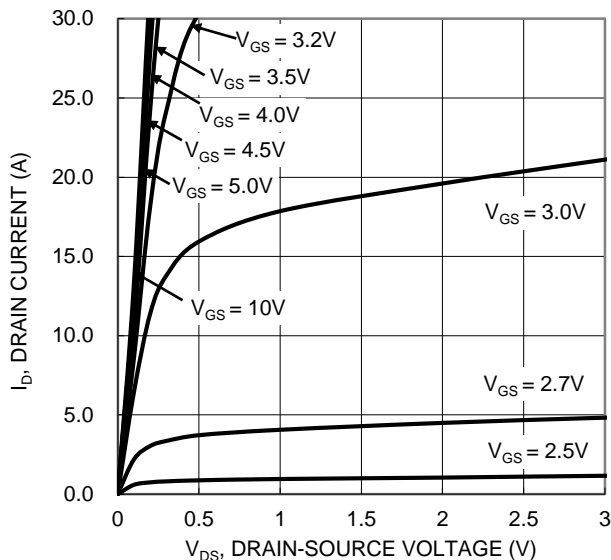


Figure 1. Typical Output Characteristic

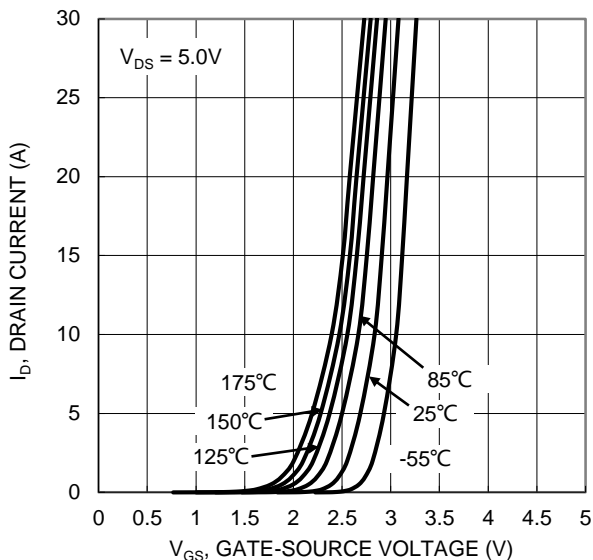


Figure 2. Typical Transfer Characteristic

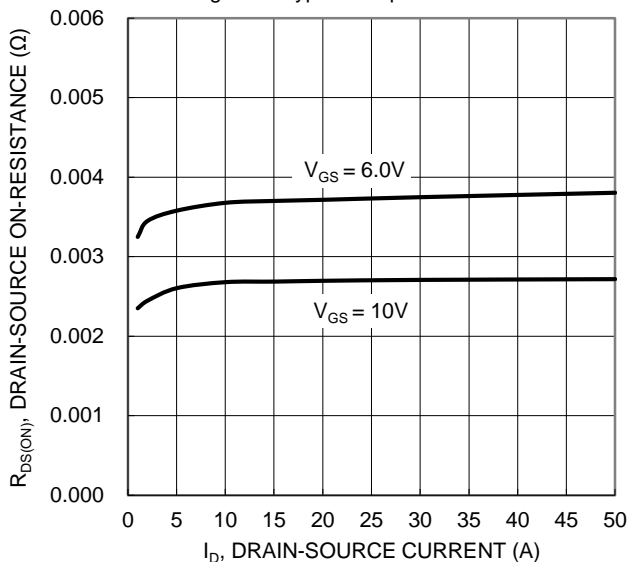


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

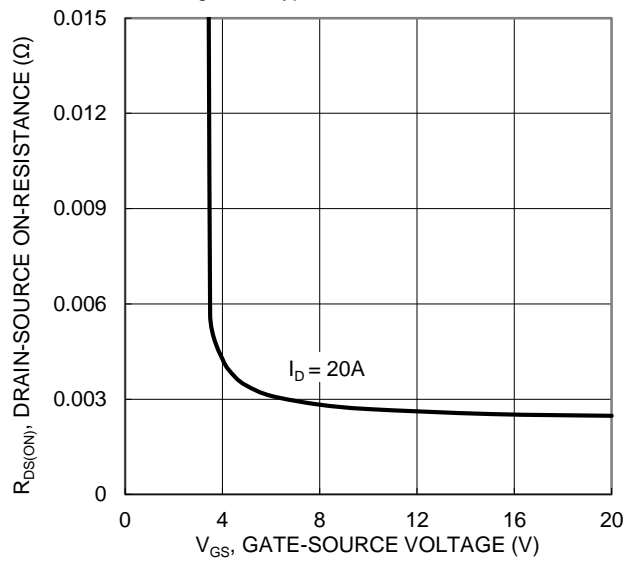


Figure 4. Typical Transfer Characteristic

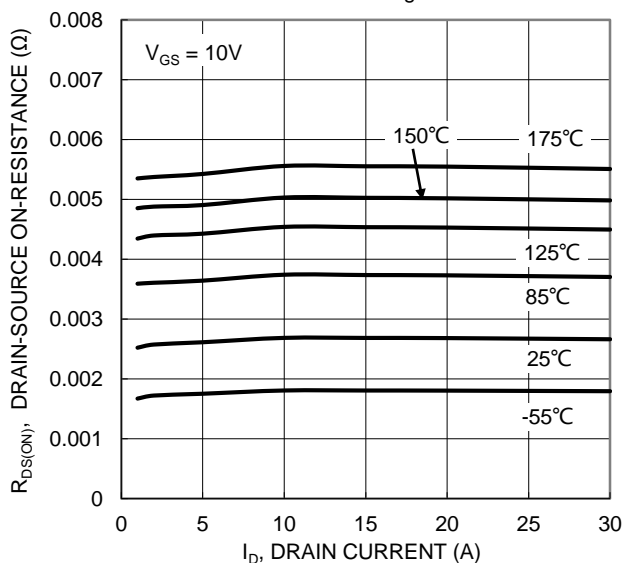


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

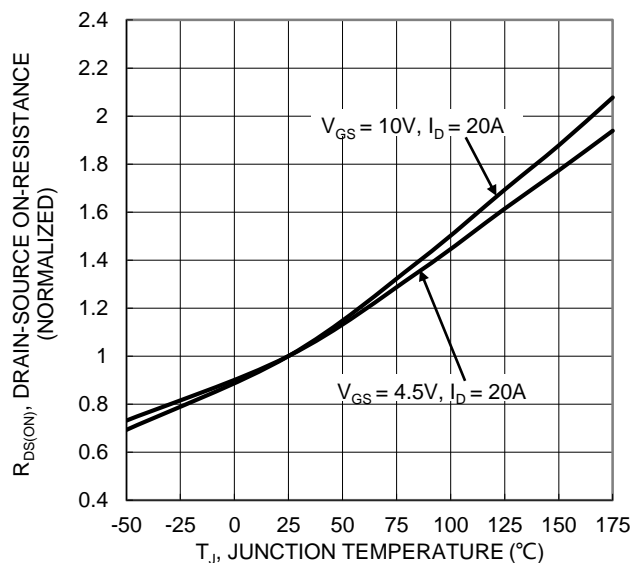


Figure 6. On-Resistance Variation with Temperature

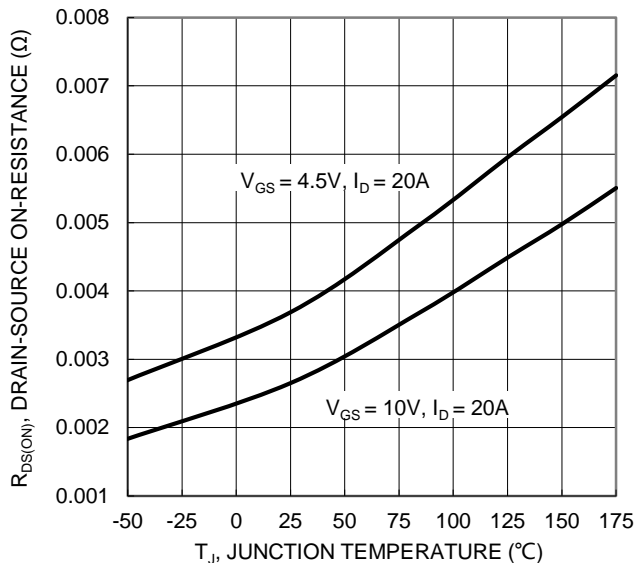


Figure 7. On-Resistance Variation with Temperature

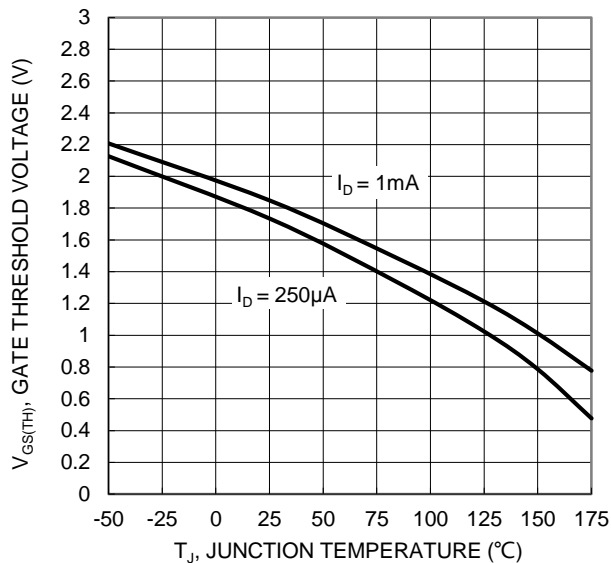


Figure 8. Gate Threshold Variation vs. Junction Temperature

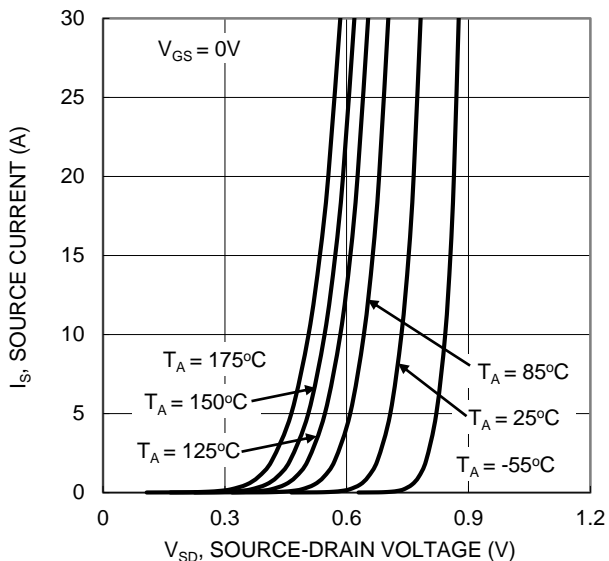


Figure 9. Diode Forward Voltage vs. Current

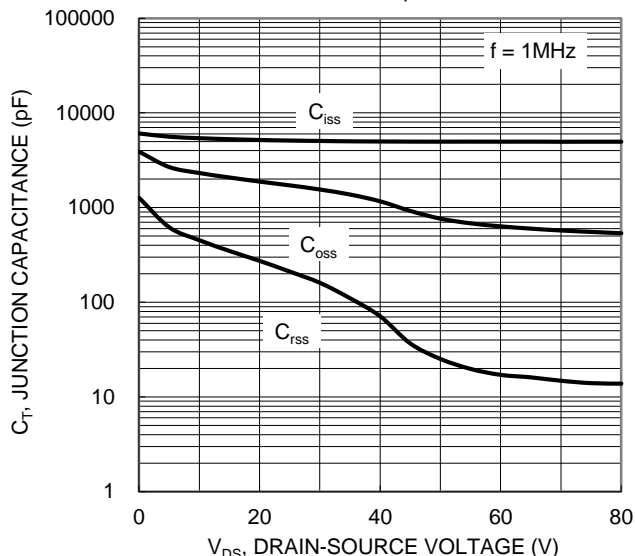


Figure 10. Typical Junction Capacitance

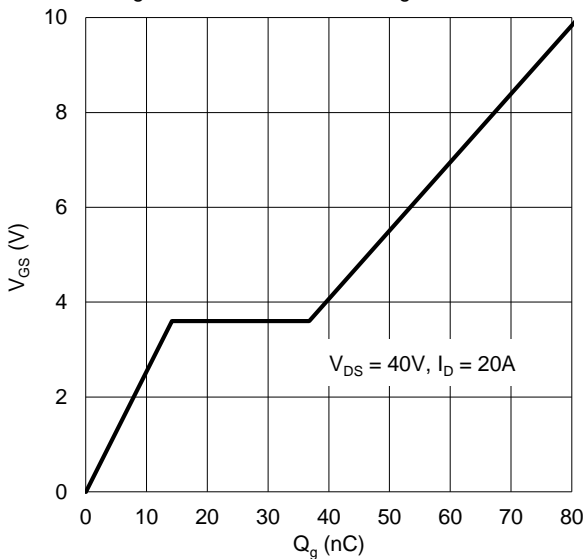


Figure 11. Gate Charge

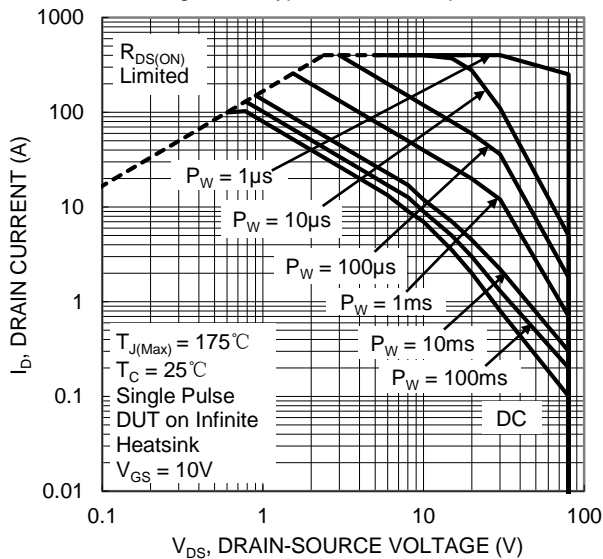


Figure 12. SOA, Safe Operation Area

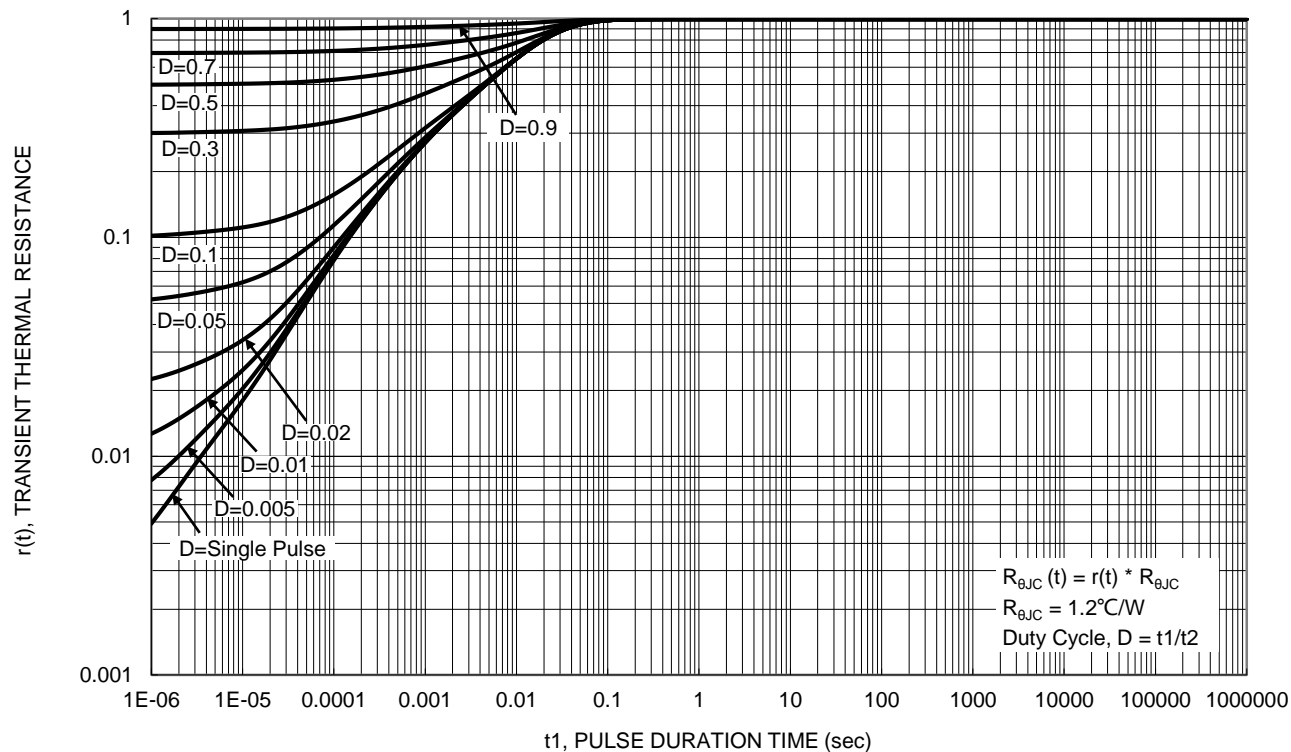
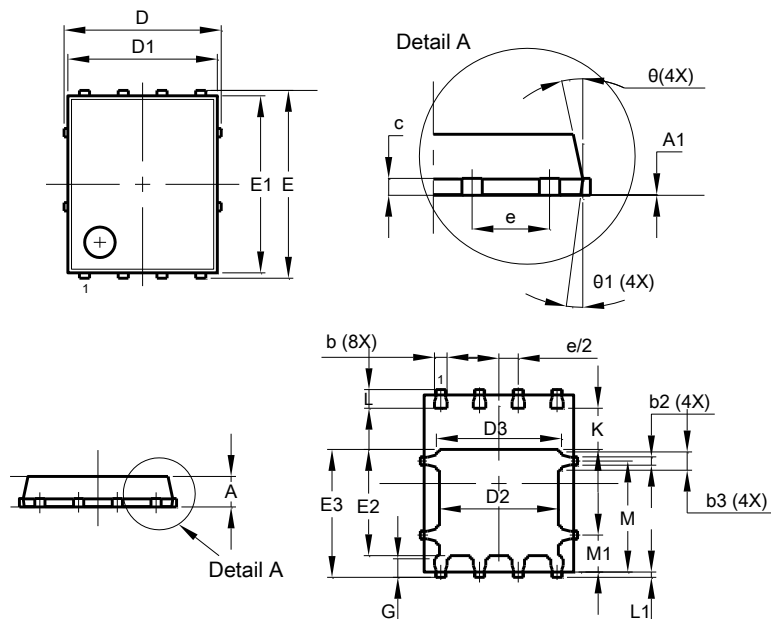


Figure 13. Transient Thermal Resistance

### Package Outline Dimensions

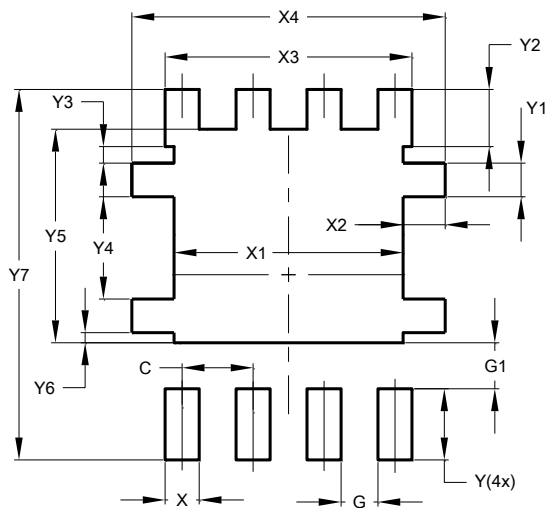
PowerDI5060-8



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
$\theta$	10°	12°	11°
$\theta1$	6°	8°	7°
All Dimensions in mm			

### Suggested Pad Layout

PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610